

PLASMA PROCESSING METHOD

ABSTRACT

In a plasma processing of generating plasma of different processing gases within a processing vessel in sequence, a setting of a high frequency power can be changed at an appropriate time point after the processing gas output from a gas supply system is changed. A power level of a second high frequency power is increased at a time point when a first parameter which reflects impedance of plasma exceeds a first threshold value after the processing gas is changed while a first high frequency power is being supplied to a first electrode or a second electrode. Further, a power level of the first high frequency power is increased at a time point when a second parameter which reflects impedance of plasma exceeds a second threshold value after the processing gas is changed while the second high frequency power is being supplied to the second electrode.

Figure 1